

<Intelligent Power Modules>

PM25RGB120

FLAT-BASE TYPE
INSULATED PACKAGE

Prepared by	A	H.Murakami, M.Joko, R.Yoneyama
		T.Marumo, T.Ogawa, T.Shimizu
Approved by		H. Takemoto
(Date)		8 th -Oct. 2015



FEATURE

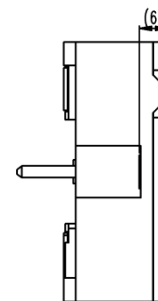
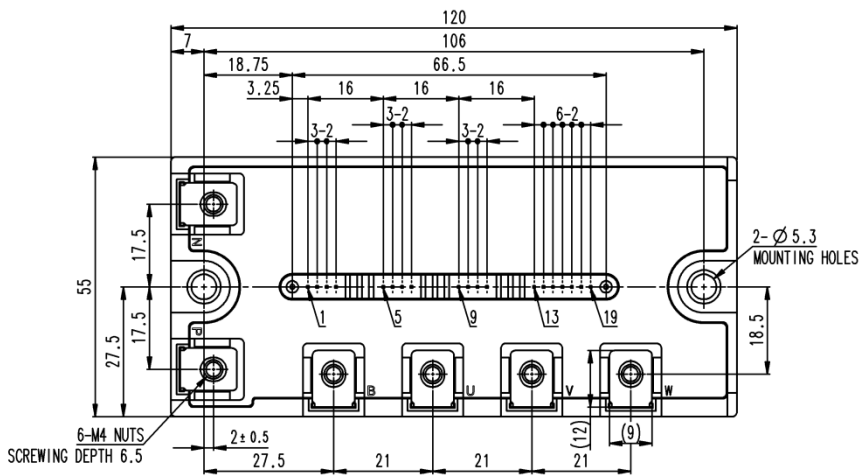
- a) Adopting Full-Gate CSTBT™ chip.
- b) The over-temperature protection which detects the chip surface temperature of CSTBT™ is adopted.
- c) Error output signal is possible from all each protection upper and lower arm of IPM.

APPLICATION

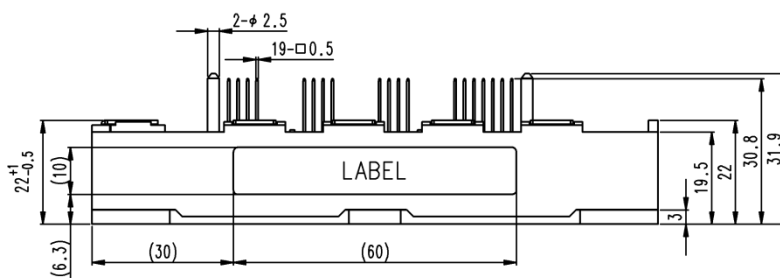
General purpose inverter, servo drives and other motor controls

PACKAGE OUTLINES

Dimensions in mm



1. VUPC
2. UFO
3. UP
4. VUP1
5. VVPC
6. VFO
7. VP
8. VVP1
9. VWPC
10. WFO
11. WP
12. VWP1
13. VNC
14. VN1
15. Br
16. UN
17. VN
18. WN
19. Fo

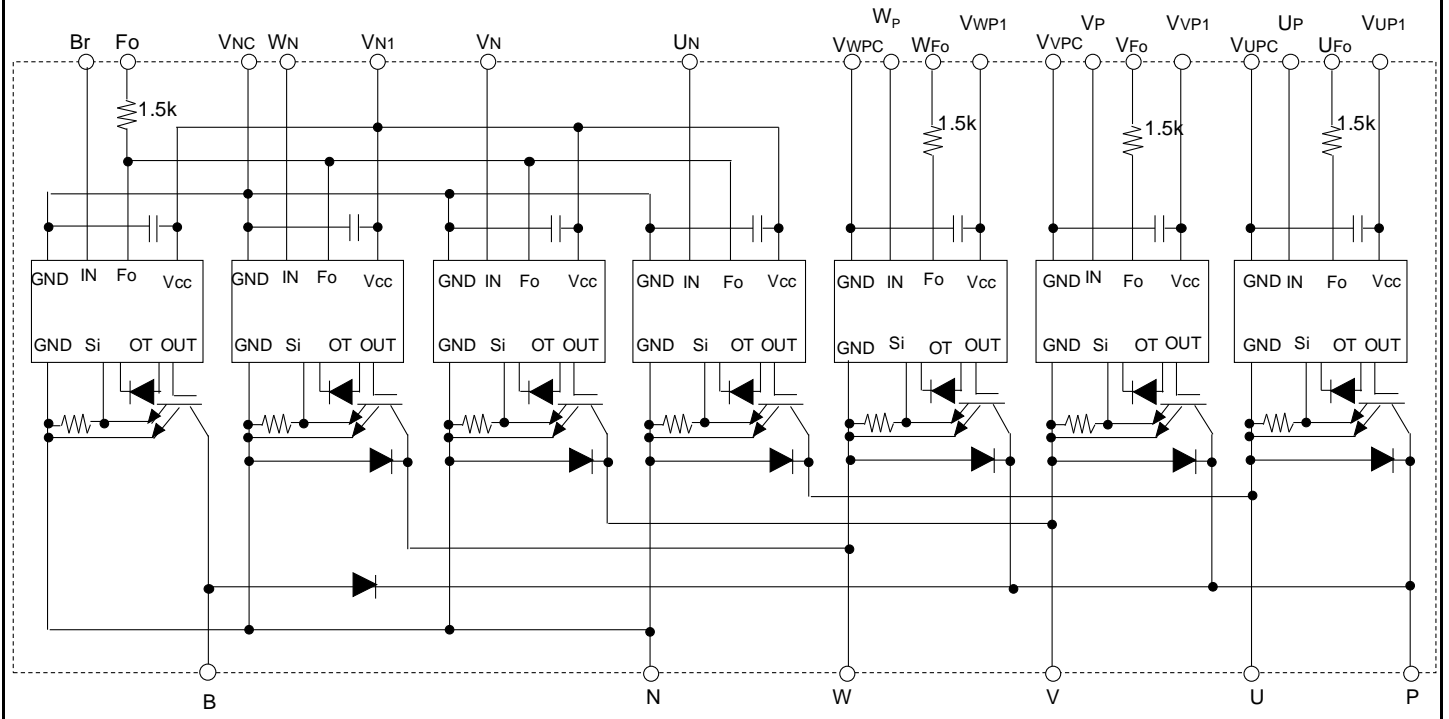


PM25RGB120

HIGH POWER SWITCHING USE
INSULATED TYPE

TENTATIVE
Notice: This is not a final specification.
Some parametric limits are subject to change

INTERNAL FUNCTIONS BLOCK DIAGRAM



MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	$V_D=15\text{ V}, V_{CIN}=15\text{ V}$	1200	V
I_C	Collector Current	$T_C=25\text{ }^\circ\text{C}$	25	A
I_{CRM}		Pulse	50	
P_{tot}	Total Power Dissipation	$T_C=25\text{ }^\circ\text{C}$	173	W
I_E	Emitter Current	$T_C=25\text{ }^\circ\text{C}$	25	A
I_{ERM}	(Free-wheeling Diode Forward current)	Pulse	50	
T_j	Junction Temperature		-20 ~ +150	$^\circ\text{C}$

*: T_c measurement point is just under the chip.

BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	$V_D=15\text{ V}, V_{CIN}=15\text{ V}$	1200	V
I_C	Collector Current	$T_C=25\text{ }^\circ\text{C}$	25	A
I_{CRM}		Pulse	50	
P_{tot}	Total Power Dissipation	$T_C=25\text{ }^\circ\text{C}$	173	W
$V_{R(DC)}$	Diode Rated Reverse DC Voltage	$T_C=25\text{ }^\circ\text{C}$	1200	V
I_F	Diode Forward Current	$T_C=25\text{ }^\circ\text{C}$	25	A
T_j	Junction Temperature		-20 ~ +150	$^\circ\text{C}$

*: T_c measurement point is just under the chip.

PM25RGB120

HIGH POWER SWITCHING USE
INSULATED TYPE

TENTATIVE
Notice: This is not a final specification.
Some parametric limits are subject to change

CONTROL PART

Symbol	Parameter	Conditions	Ratings	Unit
V_D	Supply Voltage	Applied between: $V_{UP1}-V_{UPC}$, $V_{VP1}-V_{VPC}$, $V_{WP1}-V_{WPC}$, $V_{N1}-V_{NC}$	20	V
V_{CIN}	Input Voltage	Applied between: U_P-V_{UPC} , V_P-V_{VPC} , W_P-V_{WPC} , U_N , V_N , W_N , $Br-V_{NC}$	20	V
V_{FO}	Fault Output Supply Voltage	Applied between: $U_{FO}-V_{UPC}$, $V_{FO}-V_{VPC}$, $W_{FO}-V_{WPC}$, $Fo-V_{NC}$	20	V
I_{FO}	Fault Output Current	Sink current at U_{FO} , V_{FO} , W_{FO} , Fo terminals	20	mA

TOTAL SYSTEM

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CC(prot)}$	Supply Voltage Protected by SC	$V_D = 13.5\text{ V} \sim 16.5\text{ V}$, Inverter Part, $T_j = +125^\circ\text{C}$ start	800	V
$V_{CC(surge)}$	Supply Voltage (Surge)	Applied between: P-N, Surge value	1000	V
T_{stg}	Storage Temperature	-	-40 ~ +125	$^\circ\text{C}$
V_{isol}	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base plate, AC 1min, RMS	2500	V

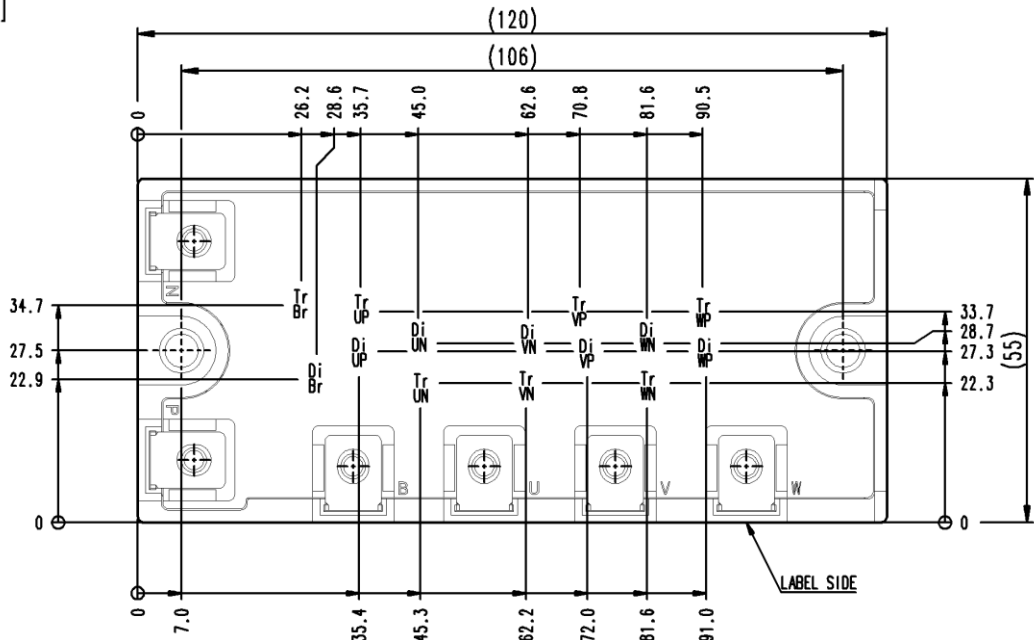
*: T_c measurement point is just under the chip.

THERMAL RESISTANCE

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal Resistance	Inverter, Junction to case, IGBT, per 1 element (Note1)	-	-	0.72	K/W
$R_{th(j-c)D}$		Inverter, Junction to case, FWD, per 1 element (Note1)	-	-	0.98	
$R_{th(j-c)Q}$		Brake, Junction to case, IGBT, per 1 element (Note1)	-	-	0.72	
$R_{th(j-c)D}$		Brake, Junction to case, Diode, per 1 element (Note1)	-	-	0.98	
$R_{th(c-s)}$	Contact Thermal Resistance	Case to heat sink, per 1 module, Thermal grease applied (Note.1)	-	0.022	-	

Note1. If you use this value, $R_{th(s-a)}$ should be measured just under the chips.

[TOP VIEW]



PM25RGB120HIGH POWER SWITCHING USE
INSULATED TYPE**TENTATIVE**
Notice: This is not a final specification.
Some parametric limits are subject to change**ELECTRICAL CHARACTERISTICS** ($T_j = 25^\circ\text{C}$, unless otherwise noted)**INVERTER PART**

Symbol	Parameter	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
V_{CEsat}	Collector-Emitter Saturation Voltage	$V_D=15\text{ V}$, $I_C=25\text{ A}$	$T_j=25^\circ\text{C}$	-	1.65	2.15	V
		$V_{CIN}=0\text{ V}$, Pulsed, Terminal (Fig.1)	$T_j=125^\circ\text{C}$	-	1.85	2.35	
V_{EC}	Emitter-Collector Voltage	$I_E=25\text{ A}$, $V_D=15\text{ V}$, $V_{CIN}=15\text{ V}$, Terminal (Fig.2)		-	1.80	2.75	V
t_{on}	Switching Time	$V_D=15\text{ V}$, $V_{CIN}=0\text{ V} \leftrightarrow 15\text{ V}$, $V_{CC}=300\text{ V}$, $I_C=25\text{ A}$, $T_j=125^\circ\text{C}$, Inductive Load (Fig.3, 4)		-	0.6	-	μs
t_{rr}				-	0.2	-	
$t_{c(on)}$				-	0.2	-	
t_{off}				-	1.1	-	
$t_{c(off)}$				-	0.4	-	
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=V_{CES}$, $V_D=15\text{ V}$, $V_{CIN}=15\text{ V}$ (Fig.5)	$T_j=25^\circ\text{C}$	-	-	1	mA
			$T_j=125^\circ\text{C}$	-	-	10	

BRAKE PART

Symbol	Parameter	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
V_{CEsat}	Collector-Emitter Saturation Voltage	$V_D=15\text{ V}$, $I_C=25\text{ A}$	$T_j=25^\circ\text{C}$	-	1.65	2.15	V
		$V_{CIN}=0\text{ V}$, Pulsed, Terminal (Fig.1)	$T_j=125^\circ\text{C}$	-	1.85	2.35	
V_{FM}	Diode Forward Voltage	$I_F=25\text{ A}$		-	1.80	2.75	V
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=V_{CES}$, $V_D=15\text{ V}$, $V_{CIN}=15\text{ V}$ (Fig.5)	$T_j=25^\circ\text{C}$	-	-	1	mA
			$T_j=125^\circ\text{C}$	-	-	10	

CONTROL PART

Symbol	Parameter	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_D	Circuit Current	$V_D=15\text{ V}$, $V_{CIN}=15\text{ V}$	$V_{P1}-V_{PC}$	-	2	4	mA
			$V_{N1}-V_{NC}$	-	8	16	
$V_{th(ON)}$	Input ON Threshold Voltage	Applied between:	1.2	1.5	1.8	V	
$V_{th(OFF)}$	Input OFF Threshold Voltage	U_P-V_{UPC} , V_P-V_{VPC} , W_P-V_{WPC} , U_N , V_N , W_N , $Br-V_{NC}$	1.7	2.0	2.3		
SC	Short Circuit Trip Level	$-20 \leq T_j \leq 125^\circ\text{C}$, $V_D=15\text{ V}$ (Fig.3, 6)	Inverter	50	-	-	A
			Brake	50	-	-	
$t_{off(SC)}$	Short Circuit Current Delay Time	$V_D=15\text{ V}$ (Fig.3, 6)	-	0.2	-	μs	
OT	Over Temperature Protection	Detect Temperature of IGBT chip	Trip level	150	-	-	$^\circ\text{C}$
			Hysteresis	-	20	-	
UV_t	Supply Circuit	$-20 \leq T_j \leq 125^\circ\text{C}$	Trip level	11.5	12.0	12.5	V
UV_r	Under-Voltage Protection		Reset level	-	12.5	-	
$I_{FO(H)}$	Fault Output Current	$V_D=15\text{ V}$, $V_{FO}=15\text{ V}$ (Note2)		-	-	0.01	mA
$I_{FO(L)}$				-	10	15	
t_{FO}	Fault Output Pulse Width	$V_D=15\text{ V}$ (Note2)	1.0	1.8	-	ms	

Note2. Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

PM25RGB120

HIGH POWER SWITCHING USE
INSULATED TYPE

TENTATIVE
Notice: This is not a final specification.
Some parametric limits are subject to change

MECHANICAL RATINGS AND CHARACTERISTICS

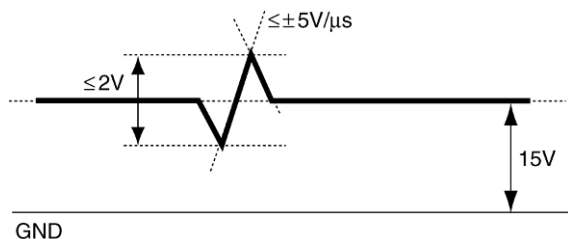
Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_s	Mounting Torque	Mounting part screw : M5	2.5	3.0	3.5	N•m
M_t	Mounting Torque	Main terminal part screw : M4	1.5	1.7	2.0	N•m
m	mass	-	-	320	-	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Conditions	Recommended value	Unit
V_{CC}	Supply Voltage	Applied across P-N terminals	≤ 800	V
V_D	Control Supply Voltage	Applied between : $V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC}, V_{N1}-V_{NC}$ (Note3)	15.0 ± 1.5	V
$V_{CIN(ON)}$	Input ON Voltage	Applied between : $U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}, U_N, V_N, W_N, Br-V_{NC}$	≤ 0.8	V
$V_{CIN(OFF)}$	Input OFF Voltage		≥ 9.0	
f_{PWM}	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
t_{dead}	Dead Time	For IPM's each input signals (Fig.7)	≥ 2.5	μs

This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note3. With ripple satisfying the following conditions: dv/dt swing $\leq \pm 5$ V/ μs , Variation ≤ 2 V peak to peak



PRECAUTIONS FOR TESTING

1. Before applying any control supply voltage (V_D), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.
After this, the specified ON and OFF level setting for each input signal should be done.
2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above V_{CES} rating of the device.
(These test should not be done by using a curve tracer or its equivalent.)

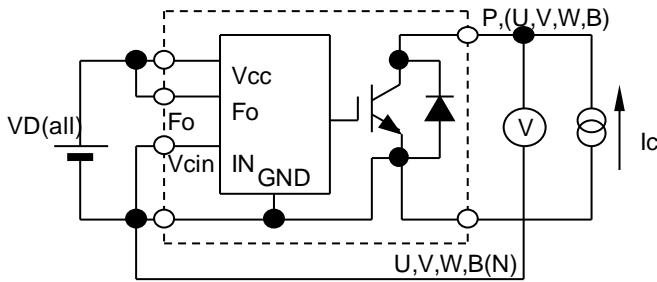


Fig.1 V_{CESat} Test

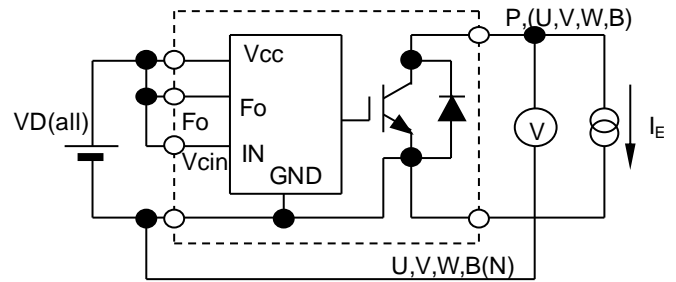


Fig.2 V_{EC} Test

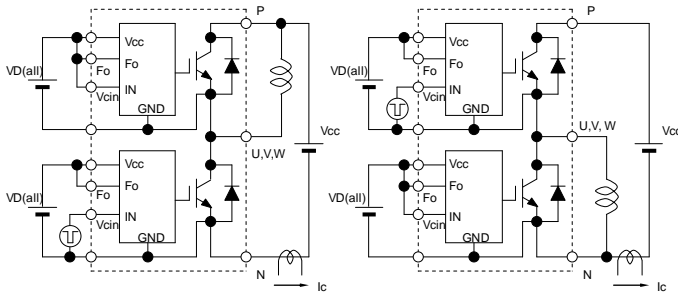


Fig.3 Switching time and SC test circuit

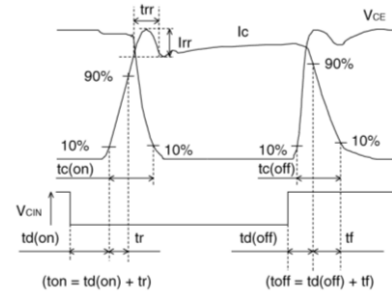


Fig.4 Switching time test waveform

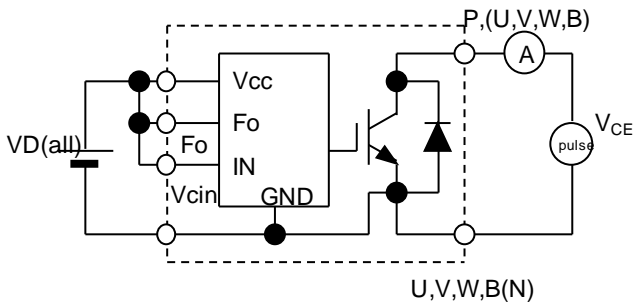


Fig.5 I_{CES} Test

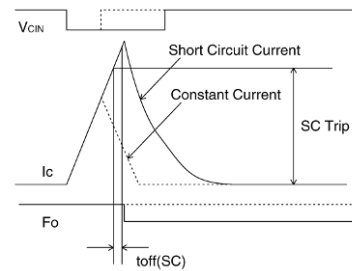
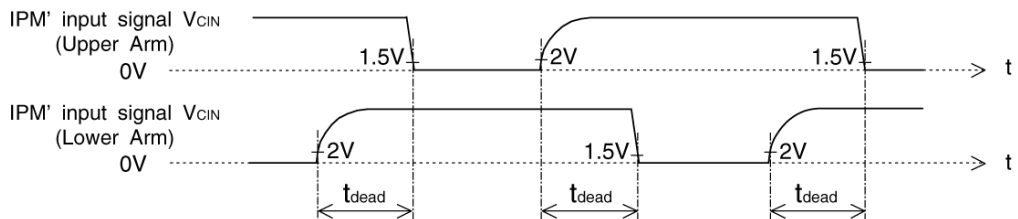


Fig.6 SC test waveform



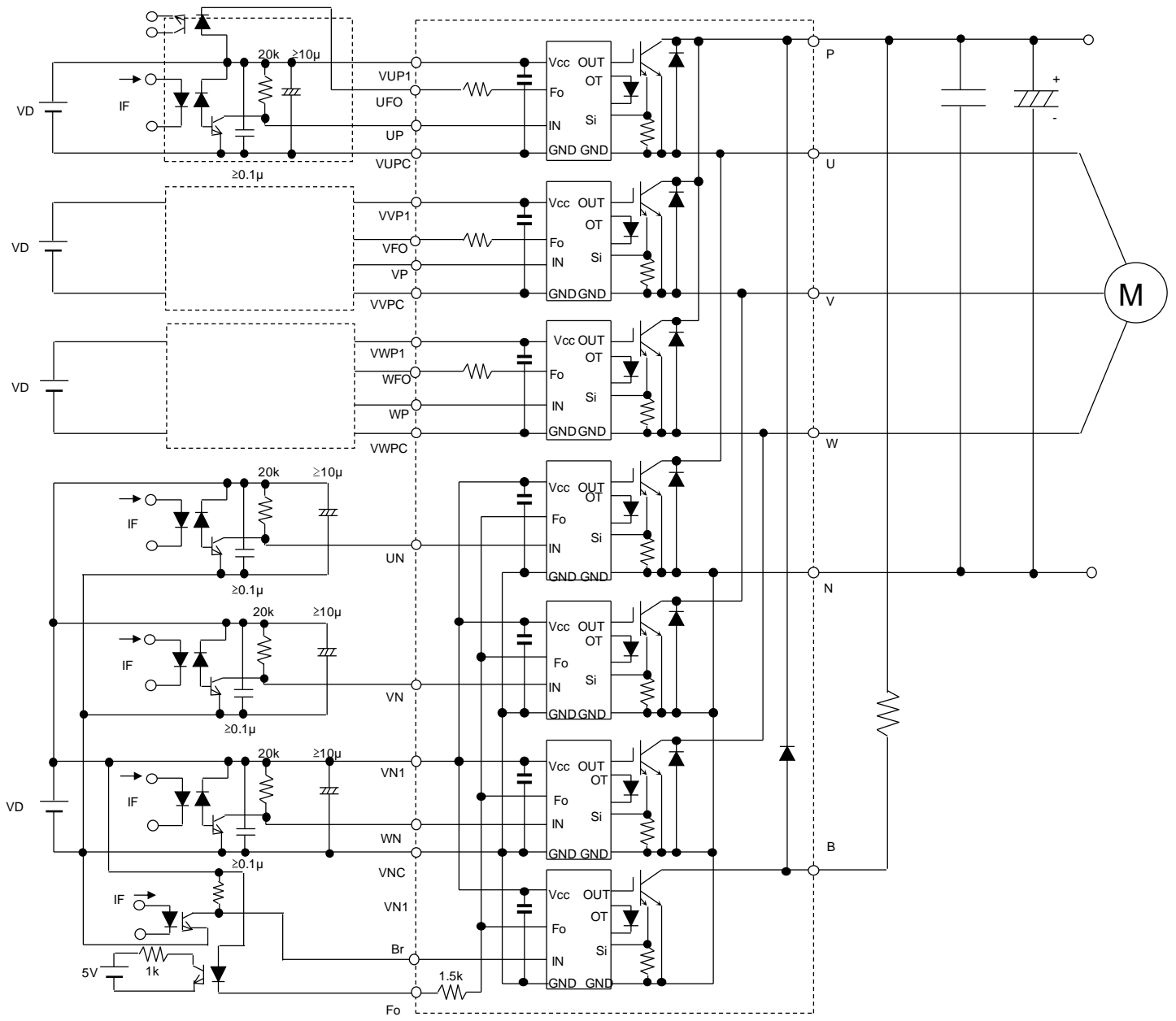
1.5V: Input on threshold voltage $V_{th(on)}$ typical value, 2V: Input off threshold voltage $V_{th(off)}$ typical value

Fig. 7 Dead time measurement point example

PM25RGB120

HIGH POWER SWITCHING USE
INSULATED TYPE

TENTATIVE
Notice: This is not a final specification.
Some parametric limits are subject to change



Interface which is the same as the U-phase

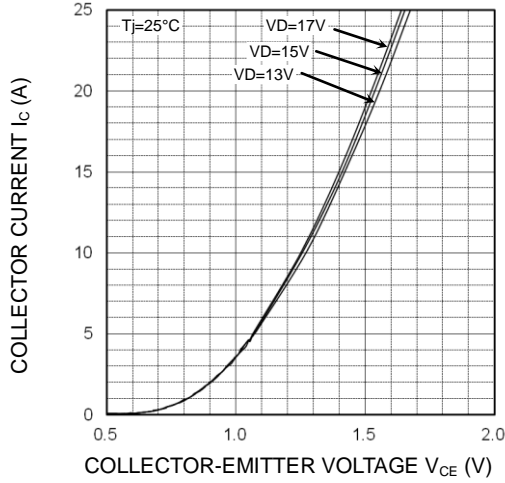
Fig. 8 Application Example Circuit

NOTES FOR STABLE AND SAFE OPERATION ;

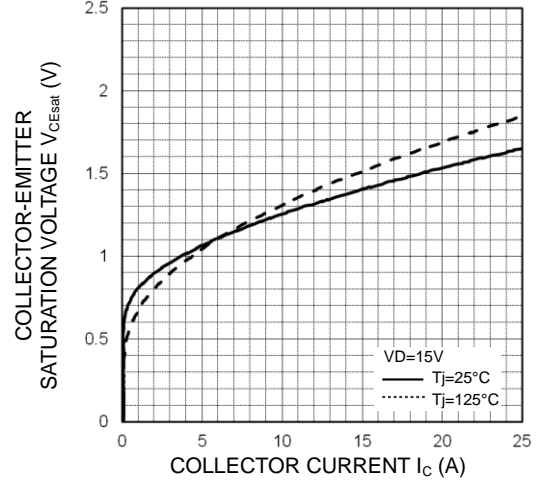
- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: $t_{PLH}, t_{PHL} \leq 0.8\mu s$, Use High CMR type.
- Slow switching opto-coupler: CTR > 100%
- Use 4 isolated control power supplies (V_D). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.

**PERFORMANCE CURVES
(Inverter Part)**

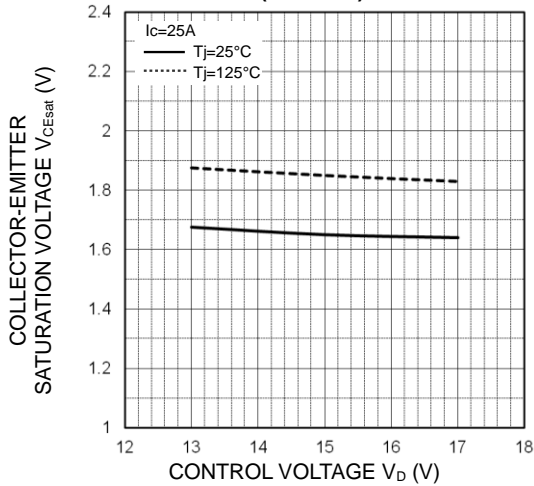
**OUTPUT CHARACTERISTICS
(TYPICAL)**



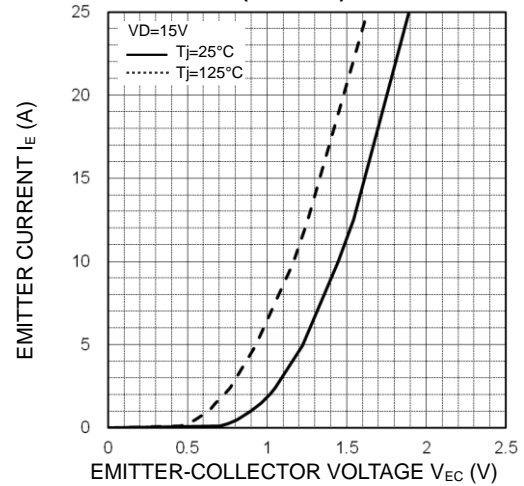
**COLLECTOR-EMITTER SATURATION
VOLTAGE (VS. Ic) CHARACTERISTICS
(TYPICAL)**



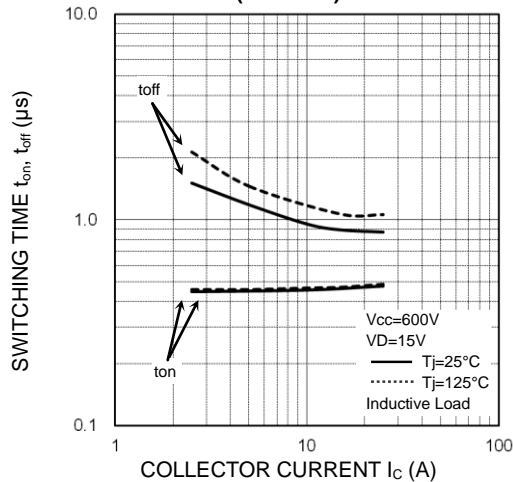
**COLLECTOR-EMITTER SATURATION
VOLTAGE (VS. Vd) CHARACTERISTICS
(TYPICAL)**



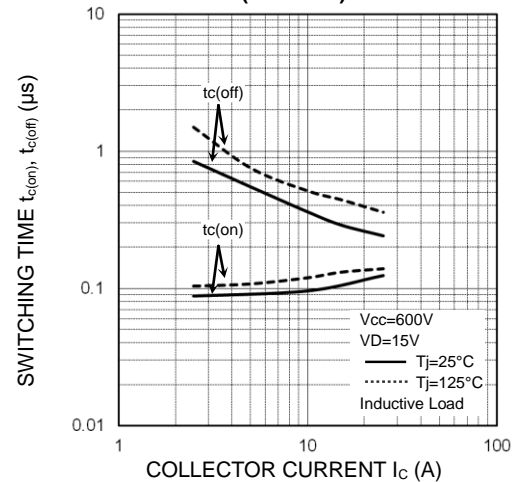
**FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**

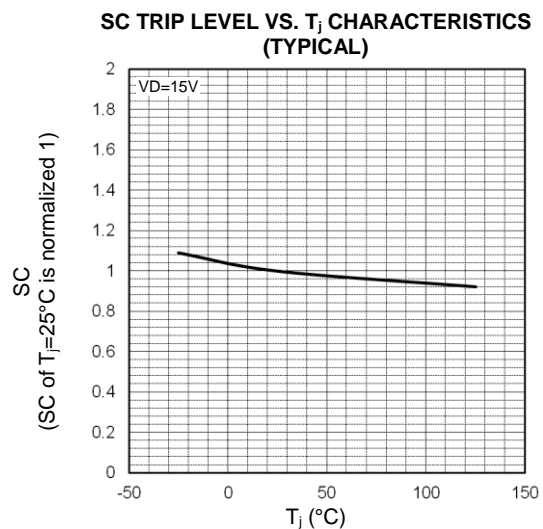
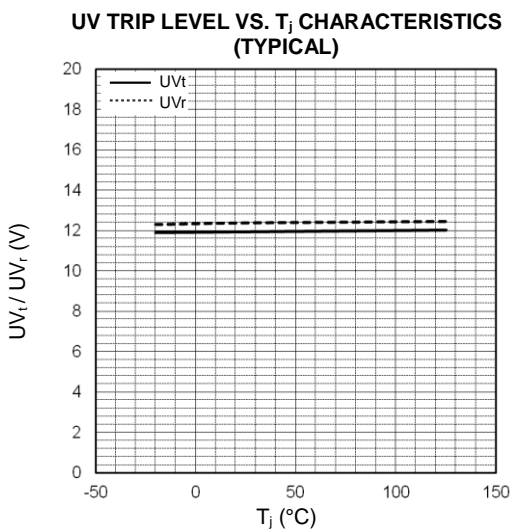
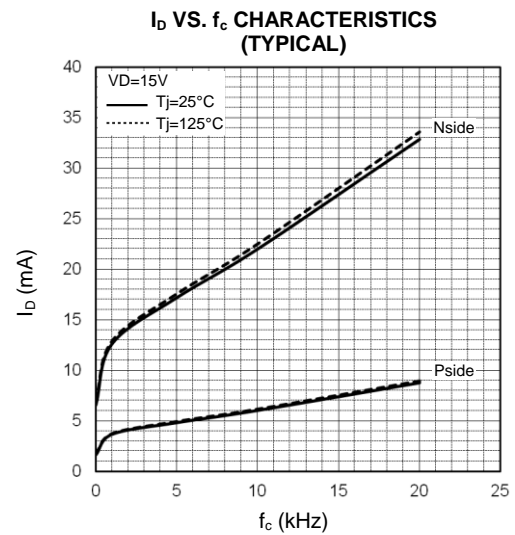
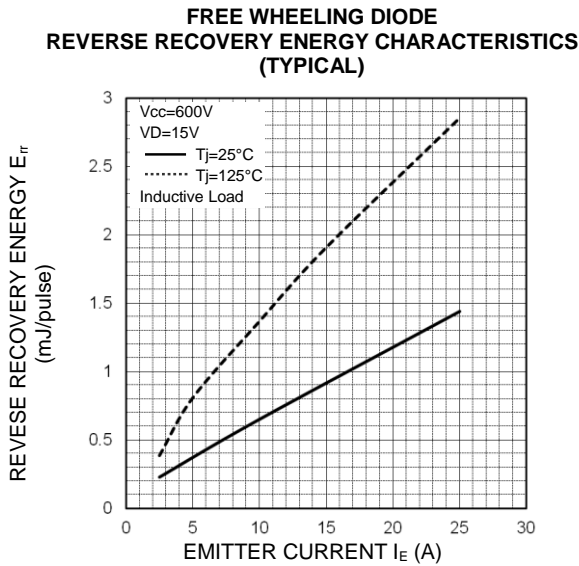
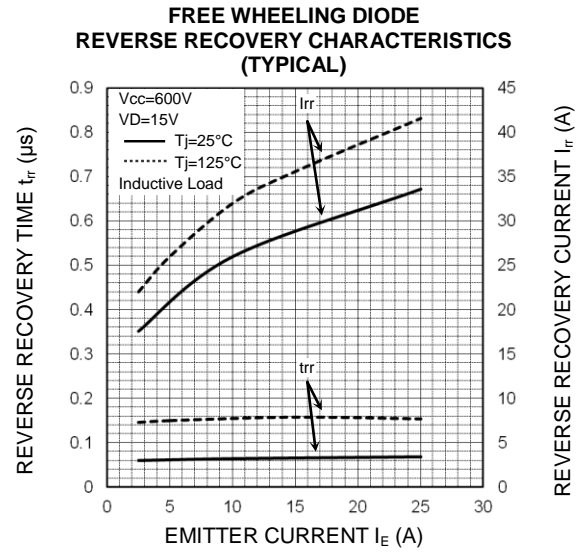
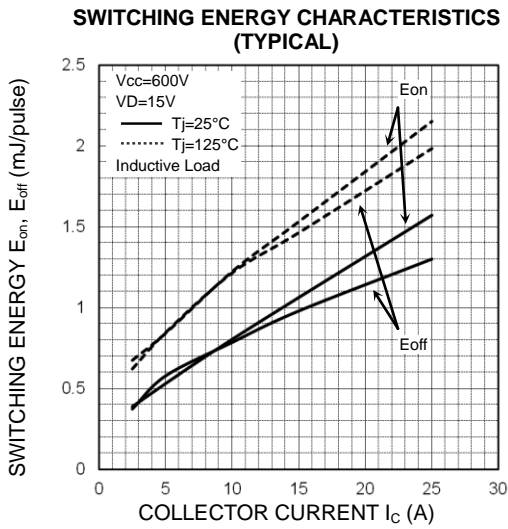


**SWITCHING TIME (ton, toff) CHARACTERISTICS
(TYPICAL)**

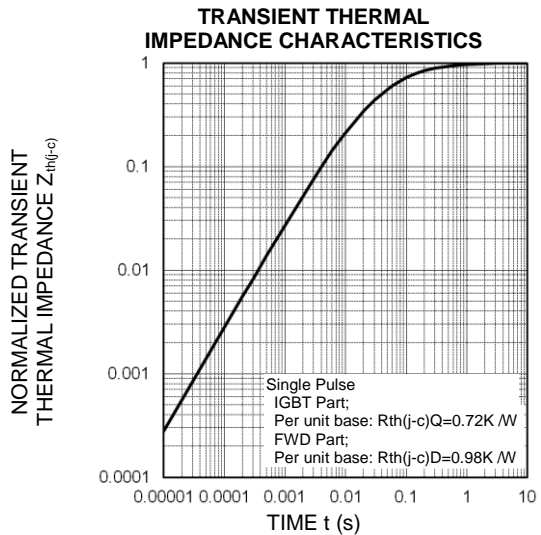
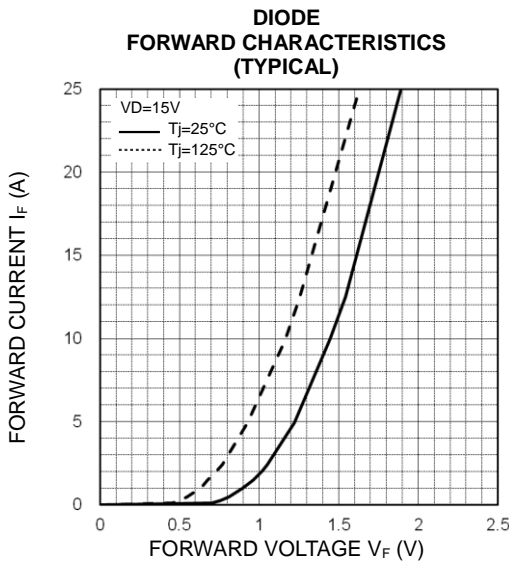
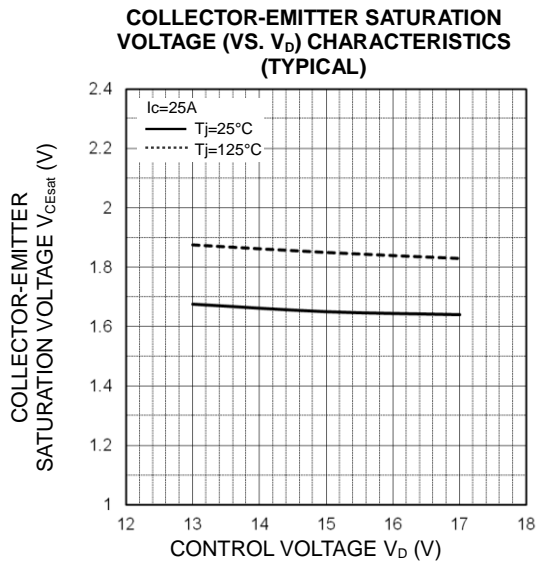
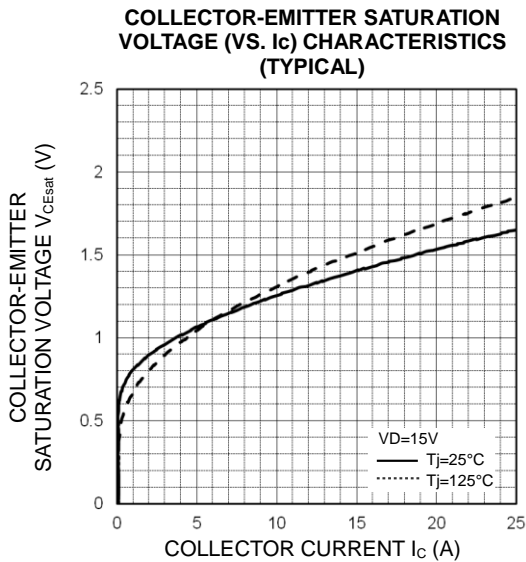
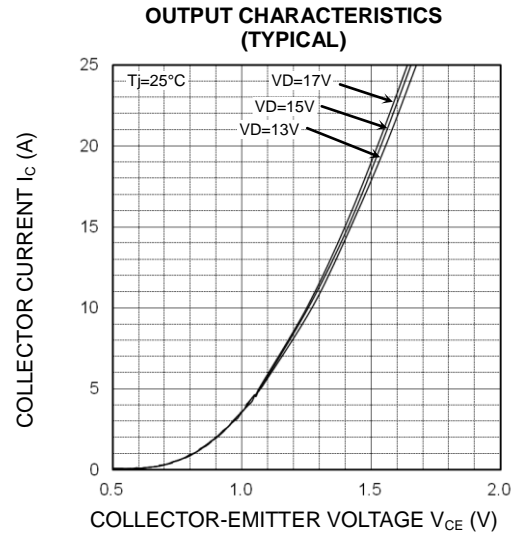
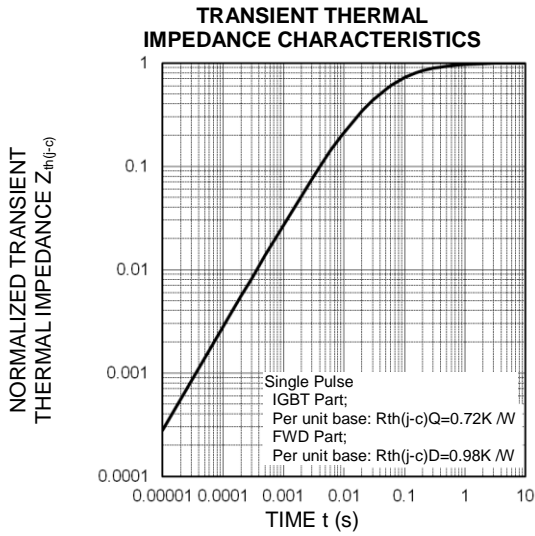


**SWITCHING TIME (tc(on), tc(off)) CHARACTERISTICS
(TYPICAL)**





(Brake Part)



Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
- Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Semiconductor home page (www.MitsubishiElectric.com/semiconductors/).
- When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
- Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
- Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Semiconductor product distributor for further details on these materials or the products contained therein.